## 5 V, 3 A Current-Mode Constant On-Time Synchronous Buck Regulator



## DESCRIPTION

The SiP12107 is a high frequency current-mode constant on-time (CM-COT) synchronous buck regulator with integrated high-side and low-side power MOSFETs. Its power stage is capable of supplying 3 A continuous current at 4 MHz switching frequency. This regulator produces an adjustable output voltage down to 0.6 V from 2.8 V to 5.5 V input rail to accommodate a variety of applications, including computing, consumer electronics, telecom, and industrial.
SiP12107's CM-COT architecture delivers ultra-fast transient response with minimum output capacitance and tight ripple regulation at very light load. No ESR or external ESR network is required for loop stability purpose. The device also incorporates a power saving scheme that significantly increases light load efficiency.
The regulator integrates a full protection feature set, including output overvoltage protection (OVP), output under voltage protection (UVP) and thermal shutdown (OTP). It also has UVLO for input rail and internal soft-start ramp.
The SiP12107 is available in lead (Pb)-free power enhanced QFN16-33G package in $3 \mathrm{~mm} \times 3 \mathrm{~mm}$ dimension.

## FEATURES

- 2.8 V to 5.5 V input voltage
- Adjustable output voltage down to 0.6 V
- 3 A continuous output current
- Programmable switching frequency up to 4 MHz
- 95 \% peak efficiency
- Supports all ceramic capacitors,no external ESR required
- Ultrafast transient response
- Selectable power saving mode or force current mode
- $\pm 1$ \% accuracy
- Pulse-by-pulse current limit
- Scalable with SiP12108-5A
- Fully protected with OTP, SCP, UVP, OVP
- $\mathrm{P}_{\mathrm{GOO}}$ D Indicator
- PowerCAD Simulation software available at www.vishay.com/power-ics/powercad-list/
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


## APPLICATIONS

- Notebook computers
- Desktop PCs and servers
- Handheld devices
- POLs for telecom
- Consumer electronics
- Industrial and automation


## TYPICAL APPLICATION CIRCUIT AND PACKAGE OPTIONS



Fig. 1 - Typical Application Circuit for SiP12107

SiP12107

| ABSOLUTE MAXIMUM RATINGS |  |  |  |
| :---: | :---: | :---: | :---: |
| ELECTRICAL PARAMETER | CONDITIONS | LIMIT | UNIT |
| $\mathrm{V}_{\text {IN }}$ | Reference to $\mathrm{P}_{\mathrm{GND}}$ | -0.3 to 6 |  |
| $\mathrm{AV}_{\text {IN }}$ | Reference to $\mathrm{A}_{\text {GND }}$ | -0.3 to 6 |  |
| LX | Reference to $\mathrm{P}_{\mathrm{GND}}$ | -0.3 to 6 | v |
| $\mathrm{A}_{\mathrm{GND}}$ to $\mathrm{P}_{\mathrm{GND}}$ |  | -0.3 to 0.3 |  |
| All logic inputs | Reference to $\mathrm{A}_{\text {GND }}$ | -0.3 to $\mathrm{AV}_{\text {IN }}+0.3$ |  |
| TEMPERATURE |  |  |  |
| Max. operating junction temperature |  | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage temperature |  | -65 to +150 |  |
| POWER DISSIPATION |  |  |  |
| Junction to ambient thermal impedance ( $\mathrm{R}_{\mathrm{th} J \mathrm{JA}}$ ) |  | 36.3 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Maximum power dissipation | Ambient temperature $=25^{\circ} \mathrm{C}$ | 3.4 | W |
|  | Ambient temperature $=100^{\circ} \mathrm{C}$ | 1.3 |  |
| ESD PROTECTION |  |  |  |
| Electrostatic discharge protection | HBM | 2 | kV |

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

| RECOMMENDED OPERATING RANGE |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
| ELECTRICAL PARAMETER | MINIMUM | TYPICAL | MAXIMUM | UNIT |
| $\mathrm{V}_{\text {IN }}$ | 2.8 | - | 5.5 | V |
| $\mathrm{AV}_{\text {IN }}$ | 2.8 | - | 5.5 |  |
| LX | -1 | - | 5.5 |  |
| $V_{\text {OUT }}$ | 0.6 | - | $0.85 \times \mathrm{V}_{\text {IN }}$ |  |
| Ambient temperature | -40 to +85 |  |  | ${ }^{\circ} \mathrm{C}$ |

## ELECTRICAL SPECIFICATIONS

| PARAMETER | SYMBOL | TEST CONDITION UNLESS OTHERWISE SPECIFIED <br> $\mathrm{V}_{\text {IN }}=A \mathrm{~V}_{\text {IN }}=3.3 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | LIMITS |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | MIN. | TYP. | MAX. |  |
| POWER SUPPLY |  |  |  |  |  |  |
| Power input voltage range | $\mathrm{V}_{\text {IN }}$ |  | 2.8 | - | 5.5 | V |
| Bias input voltage range | $\mathrm{AV}_{\text {IN }}$ |  | 2.8 | - | 5.5 |  |
| Input current | IVIN_NoLoad | $\begin{gathered} \text { Device switching, } \mathrm{I}_{\mathrm{O}}=0 \mathrm{~A}, \\ \mathrm{R}_{\mathrm{on}}=100 \mathrm{k} \Omega, \text { AUTO }=\text { Low } \end{gathered}$ | - | 1000 | - | $\mu \mathrm{A}$ |
| Shutdown current | $\mathrm{IV}_{\text {IN_SHDN }}$ | $\mathrm{EN}=0 \mathrm{~V}$ | - | 6 | 12 |  |
| $\mathrm{AV}_{\text {IN }}$ UVLO threshold | $\mathrm{AV}_{\mathrm{IN}^{1}}, \mathrm{U}_{\mathrm{VLO}}$ | $\mathrm{AV}_{\text {IN }}$ rising edge | - | 2.55 | - | V |
| $\mathrm{AV}_{\text {IN }}$ UVLO hysteresis | $\mathrm{U}_{\mathrm{VL} \text { LOHYS }}$ |  | - | 300 | - | mV |
| PWM CONTROLLER |  |  |  |  |  |  |
| Feedback reference | $V_{\text {FB }}$ | $\mathrm{T}_{\mathrm{A}}=0^{\circ} \mathrm{C}$ to $+70^{\circ} \mathrm{C}$ | 0.594 | 0.600 | 0.606 | V |
|  |  | $\mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $+85{ }^{\circ} \mathrm{C}$ | 0.591 | 0.600 | 0.609 |  |
| $\mathrm{V}_{\mathrm{FB}}$ input bias current |  |  | - | 2 | 200 | nA |
| Transconductance |  |  | - | 1 | - | mS |
| COMP source current |  |  | - | 50 | - | $\mu \mathrm{A}$ |
| COMP sink current |  |  | - | 50 | - |  |
| Switching frequency range |  | Guaranteed by design | 0.2 | - | 4 | MHz |
| Minimum on-time |  | Guaranteed by design | - | 50 | - | ns |
| Minimum off-time |  | $\mathrm{V}_{\text {OUT }}=1.2 \mathrm{~V}, \mathrm{R}_{\text {ON }}=100 \mathrm{k} \Omega$ | - | 120 | - |  |
| Soft start time |  |  | - | 1.5 | - | ms |
| INTEGRATED MOSFETs |  |  |  |  |  |  |
| High-side on resistance |  | $\mathrm{V}_{\mathrm{IN}}=3.3 \mathrm{~V}$ | - | 56 | - | $\mathrm{m} \Omega$ |
| Low-side on resistance |  |  | - | 33 | - |  |
| FAULT PROTECTIONS |  |  |  |  |  |  |
| Over current limit |  | Inductor valley current | - | 4.5 | - | A |
| Output OVP threshold |  | $\mathrm{V}_{\text {FB }}$ with respect to 0.6 V reference | - | 20 | - | \% |
| Output UVP threshold |  |  | - | -25 | - |  |
| Over temperature protection |  | Rising temperature | - | 160 | - | ${ }^{\circ} \mathrm{C}$ |
|  |  | Hysteresis | - | 35 | - |  |
| POWER GOOD |  |  |  |  |  |  |
| Power good output threshold |  | $\mathrm{V}_{\mathrm{FB}}$ rising above 0.6 V reference | - | 20 | - | \% |
|  |  | $\mathrm{V}_{\mathrm{FB}}$ falling below 0.6 V reference | - | -10 | - |  |
| Power good on resistance |  |  | - | 30 | - | $\Omega$ |
| Power good delay time |  |  | - | 6 | - | $\mu \mathrm{s}$ |
| ENABLE THRESHOLD |  |  |  |  |  |  |
| Logic high level |  |  | 1.5 | - | - | V |
| Logic low level |  |  | - | - | 0.4 |  |

## FUNCTIONAL BLOCK DIAGRAM



Fig. 2 - SiP12107 Functional Block Diagram

| ORDERING INFORMATION |  |  |  |
| :--- | :---: | :---: | :---: |
| PART NUMBER | PACKAGE | MARKING <br> (LINE 2: P/N) |  |
| SIP12107DMP-T1-GE3 | QFN16-33G | 2107 |  |
| SIP12107DB |  |  |  |

## $\begin{array}{ll}\mathrm{O} & \mathrm{P} / \mathrm{N} \\ \boldsymbol{G A} \quad \mathrm{AA}\end{array}$ <br> W11B

Format:
Line 1: dot
Line 2: P/N
Line 2: Siliconix logo and ESD symbol
Line 3: factory code and year code and work week code and lot code

## PIN CONFIGURATION



QFN16-33G

Fig. 3 - SiP12107 Pin Configuration (Top View)

| PIN CONFIGURATION |  |  |
| :---: | :---: | :---: |
| PIN NUMBER | NAME | FUNCTION |
| 1 | $\mathrm{V}_{\text {IN }}$ | Input supply voltage for power MOS. $\mathrm{V}_{\text {IN }}=2.8 \mathrm{~V}$ to 5.5 V |
| 2 | $\mathrm{AV}_{\text {IN }}$ | Input supply voltage for internal circuitry. $\mathrm{AV}_{\text {IN }}=2.8 \mathrm{~V}$ to 5.5 V |
| 3 | EN | Enable pin. Enable > 1.5 V |
| 4 | Ron | An external resistor between R $\mathrm{R}_{\text {ON }}$ and GND sets the switching on time |
| 5 | AUTO | Sets switching mode AUTO to $A V_{\text {IN }}=$ PWM, AUTO to GND = light load mode |
| 6 | $\mathrm{P}_{\mathrm{GD}}$ | Power good output. Open drain |
| 7 | GMO | Connect to an external RC network for loop compensation and droop function |
| 8 | $\mathrm{A}_{\text {GND }}$ | Analog ground |
| 9 | $\mathrm{V}_{\text {FB }}$ | Feedback voltage. 0.6 V (typ.) |
| 10 | $\mathrm{V}_{\text {OUT }}$ | $\mathrm{V}_{\text {OUT }}$, output voltage sense connection |
| 11 | LX | Switching output, inductor connection point |
| 12 | LX | Switching output, inductor connection point |
| 13 | LX | Switching output, inductor connection point |
| 14 | $\mathrm{P}_{\text {GND }}$ | Power ground |
| 15 | $\mathrm{P}_{\text {GND }}$ | Power ground |
| 16 | $\mathrm{V}_{\text {IN }}$ | Input supply voltage for power MOS. $\mathrm{V}_{\text {IN }}=2.8 \mathrm{~V}$ to 5.5 V |

ELECTRICAL CHARACTERISTICS $\left(\mathrm{V}_{\mathrm{IN}}=3.3 \mathrm{~V}, \mathrm{~L}=1 \mu \mathrm{H}, \mathrm{C}=3 \times 22 \mu \mathrm{~F}, \mathrm{f}_{\mathrm{SW}}=1.2 \mathrm{MHz}\right.$ unless noted otherwise)


Efficiency vs. IOUT (PSM)


Load Regulation: \% of VOUT vs. IOUt (PSM)


Line Regulation $1.2 \mathrm{~V}_{\text {OUT }}$ Nominal 0 A Load (PSM)


Efficiency vs. Iout (PWM)


Load Regulation: \% of $\mathrm{V}_{\text {OUt }}$ vs. $\mathrm{I}_{\text {OUT }}$ (PWM)


Line Regulation 1.2 $\mathrm{V}_{\text {OUt }}$ at 3 A Load (PWM)

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Fsw $_{\text {Sw }}$ Variation vs. Iout (PSM)


Output Ripple PSM: 0 A Load


Output Ripple PWM: 0 A Load


Fsw $_{\text {Sw }}$ Variation vs. Iout (PWM)


Output Ripple PSM: 0 A Load


Output Ripple PWM: 3 A Load

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Vishay Siliconix


Startup PSM: 0 A Load


Startup PSM: 3 A Load


Startup PWM: 0 A Load


Shutdown PSM: 0 A Load


Shutdown PSM: 3 A Load


Shutdown PWM: 0 A Load

SiP12107


Startup PWM: 3 A Load


Load Step PSM: O A to 1.5 A Load (undershoot)


Load Step PSM: 0A to 3 A Load (undershoot)


Shutdown PWM: 3 A Load


Load Step PSM O A to 1.5 A Load (overshoot)


Load Step PSM: 0 A to 3 A Load (overshoot)

SiP12107
Vishay Siliconix


Load Step PWM: O A to 1.5 A Load (undershoot)


Load Step PWM: 0 A to 3 A Load (undershoot)


Load Step PWM O A to 1.5 A Load (overshoot)


Load Step PWM 0 A to 3 A Load (overshoot)

## OPERATIONAL DESCRIPTION

## Device Overview

SiP12107 is a high-efficiency monolithic synchronous buck regulator capable of delivering up to 3 A continuous current. The device has programmable switching frequency up to 4 MHz . The control scheme is based on current-mode constant-on-time architecture, which delivers fast transient response and minimizes external components. Thanks to the internal current ramp information, no high-ESR output bulk or virtual ESR network is required for the loop stability. This device also incorporates Power-Saving feature by enabling diode emulation mode and frequency foldback as load decrease.
SiP12107 has a full set of protection and monitoring features:

- Over current protection in pulse-by-pulse mode
- Output over voltage protection
- Output under voltage protection with device latch
- Over temperature protection with hysteresis
- Dedicated enable pin for easy power sequencing
- Power good open drain output

This device is available in QFN16 $3 \times 3$ package to deliver high power density and minimize PCB area.

## Power Stage

SiP12107 integrates a high-performance power stage with a $\sim 64 \mathrm{~m} \Omega \mathrm{p}$-channel MOSFET and a $\sim 33 \mathrm{~m} \Omega \mathrm{n}$-channel MOSFET. The MOSFETs are optimized to achieve $95 \%$ efficiency at 2 MHz switching frequency.
The power input voltage $\left(\mathrm{V}_{\mathrm{IN}}\right)$ can go up to 5.5 V and down as low as 2.8 V for the power conversion. The logic bias voltage ( $\mathrm{AV}_{\mathrm{IN}}$ ) ranges from 2.8 V to 5.5 V .

## PWM Control Mechanism

SiP12107 employs a state-of-the-art current-mode COT control mechanism. During steady-state operation, output voltage is compared with internal reference ( 0.6 V typ.) and the amplified error signal ( $\mathrm{V}_{\mathrm{COMP}}$ ) is generated on the COMP pin. In the meantime, inductor valley current is sensed, and its slope ( $l_{\text {sense }}$ ) is converted into a voltage signal ( $\mathrm{V}_{\text {current }}$ ) to be compared with $\mathrm{V}_{\text {COMP }}$. Once $\mathrm{V}_{\text {current }}$ is lower than $\mathrm{V}_{\text {COMP }}$, a single shot on-time is generated for a fixed time programmed by the external $\mathrm{R}_{\mathrm{ON}}$. Fig. 4 illustrates the basic block diagram for CM-COT architecture and Fig. 5 demonstrates the basic operational principle:


Fig. 4 - CM-COT Block Diagram


Fig. 5 - CM-COT Operational Principle

The following equation illustrates the relationship between on-time, $\mathrm{V}_{\mathrm{IN}}, \mathrm{V}_{\mathrm{OUT}}$ and $\mathrm{R}_{\mathrm{ON}}$ value:
$T_{\mathrm{ON}}=\mathrm{R}_{\mathrm{ON}} \times K \times \frac{\mathrm{V}_{\mathrm{OUT}}}{\mathrm{V}_{\text {IN }}}$, where $\mathrm{K}=9.6 \times 10^{-12}$ a constant set internally

Once on-time is set, the pseudo constant frequency is then determined by the following equation:

$$
f s w=\frac{\mathrm{D}}{\mathrm{~T}_{\mathrm{ON}}}=\frac{\frac{\mathrm{V}_{\mathrm{OUT}}}{\mathrm{~V}_{\mathrm{IN}}}}{\frac{\mathrm{~V}_{\mathrm{OUT}}}{\mathrm{~V}_{\mathrm{IN}}} \times \mathrm{R}_{\mathrm{ON}} \times \mathrm{K}}=\frac{1}{\mathrm{R}_{\mathrm{ON}} \times \mathrm{K}}
$$

## Loop Stability and Compensator Design

Due to the nature of current mode control, a simple RC network (type II compensator) is required between COMP and $A_{G N D}$ for loop stability and transient response purpose. General concept of this loop design is to introduce a single zero through the compensator to determine the crossover frequency of overall close loop system.

The overall loop can be broken down into following segments.
Output feedback divider transfer function $\mathrm{H}_{\mathrm{fb}}$ :

$$
H_{f b}=\frac{R_{\mathrm{fb} 2}}{R_{\mathrm{fb} 1} \times R_{\mathrm{fb} 2}}
$$

Voltage compensator transfer function $G_{\text {COMP }}(s)$ :

$$
\mathrm{G}_{\mathrm{COMP}}(\mathrm{~s})=\frac{\mathrm{R}_{\mathrm{O}} \times\left(1+\mathrm{s} \mathrm{C}_{\mathrm{COMP}} \mathrm{R}_{\mathrm{COMP}}\right)}{\left(1+\mathrm{s} \mathrm{R}_{\mathrm{O}} \mathrm{C}_{\mathrm{COMP}}\right)} \mathrm{gm}
$$

Modulator transfer function $\mathrm{H}_{\text {mod }}(\mathrm{s}):$

$$
\mathrm{H}_{\text {mod }}(\mathrm{s})=\frac{1}{\mathrm{AV}_{1} \times \mathrm{R}_{\mathrm{DS}(\text { on })}} \times \frac{\mathrm{R}_{\text {load }} \times\left(1+\mathrm{sC}_{\mathrm{O}} \mathrm{R}_{\text {ESR }}\right)}{\left(1+\mathrm{sC}_{\mathrm{O}} \mathrm{R}_{\text {load }}\right)}
$$

The complete loop transfer function is given by:

$$
H_{\text {mod }}(s)=\frac{R_{\text {fb2 }}}{R_{\mathrm{fb} 1} \times R_{\mathrm{fb} 2}} \times \frac{\mathrm{R}_{\mathrm{O}} \times\left(1+s \mathrm{C}_{\mathrm{COMP}} R_{\mathrm{COMP}}\right)}{\left(1+\mathrm{sR} \mathrm{R}_{\mathrm{O}} \mathrm{C}_{\mathrm{COMP}}\right)} g m \times \frac{1}{\mathrm{AV}_{1} \times R_{\mathrm{DS}(\mathrm{on})}} \times \frac{R_{\text {load }} \times\left(1+s \mathrm{C}_{\mathrm{O}} R_{\mathrm{ESR}}\right)}{\left(1+\mathrm{sC} \mathrm{C}_{\mathrm{O}} R_{\mathrm{load}}\right)}
$$

When:

| $\mathrm{C}_{\mathrm{COMP}}=$ compensation capacitor | $\mathrm{R}_{\mathrm{DS}(\mathrm{on})}=\mathrm{LS}$ switch resistance |  |
| :--- | :--- | :--- |
| $\mathrm{R}_{\mathrm{COMP}}=$ compensation resistor | $\mathrm{R}_{\mathrm{fb} 1}=$ feedback resistor connect to LX |  |
| gm | $=$ error amplifier transconductance | $\mathrm{R}_{\mathrm{fb} 2}=$ feedback resistor connect to ground |
| $\mathrm{R}_{\text {load }}=$ load resistance | $\mathrm{R}_{\mathrm{O}}$ | $=$ output impedance of error amplifier $=20 \mathrm{M} \Omega$ |
| $\mathrm{C}_{\mathrm{O}}$ | $=$ output capacitor | $\mathrm{AV}_{1}$ |
|  |  | $=$ voltage to current gain $=3$ |

## Power-Saving Mode Operation

To further improve efficiency at light-load condition, SiP12107 provides a set of innovative implementations to eliminate LS recirculating current and switching losses. The internal zero crossing detector (ZCD) monitors LX node voltage to determine when inductor current starts to flow negatively. In power saving mode (PSM), as soon as inductor valley current crosses zero, the device first deploys diode emulation mode by turning off LS FET. If load further decreases, switching frequency is further reduced
proportional to load condition to save switching losses while keeping output ripple within tolerance. The switching frequency is set by the controller to maintain regulation. At zero load this frequency can go as low as hundreds of Hz .
Whenever fixed frequency PWM operation is required over the entire load span, power saving mode feature can be disabled by connecting AUTO pin to $\mathrm{V}_{\text {IN }}$ or $A V_{\text {IN }}$.

## OUTPUT MONITORING AND PROTECTION FEATURES

## Output Over-Current Protection (OCP)

SiP12107 has pulse-by-pulse over-current limit control. The inductor valley current is monitored during LS FET turn-on period through $R_{D S(o n)}$ sensing. After a pre-defined time, the valley current is compared with internal threshold (5 A typ.) to determine the threshold for OCP. If monitored current is higher than threshold, HS turn-on pulse is skipped and LS FET is kept on until the valley current returns below OCP limit.

In the severe over-current condition, pulse-by-pulse current limit eventually triggers output under-voltage protection (UVP), which latches the device off to prevent catastrophic thermal-related failure. UVP is described in the next section. OCP is enabled immediately after $\mathrm{AV}_{\text {IN }}$ passes UVLO level. Figure 6 illustrates the OCP operation.


Fig. 6-Over-Current Protection Illustration

## Output Under-Voltage Protection (UVP)

UVP is implemented by monitoring output through $V_{F B}$ pin. Once the voltage level at $\mathrm{V}_{\mathrm{FB}}$ is below 0.45 V for more than $20 \mu \mathrm{~s}$, then UVP event is recognized and both HS and LS MOSFETs are turned off. UVP latches the device off until either $A V_{\mathbb{I N}}$ or $E N$ is recycled.
UVP is only active after the completion of soft-start sequence.

## Output Over-Voltage Protection (OVP)

For OVP implementation, output is monitored through FB pin. After soft-start, if the voltage level at FB is above 20 \% (typ.), OVP is triggered with HS FET turning off and LS FET turning on immediately to discharge the output. Normal operation is resumed once FB voltage drops back to 0.6 V . OVP is active immediately after $A V_{\mathbb{I N}}$ passes UVLO level.

## Over-Temperature Protection (OTP)

SiP12017 has internal thermal monitor block that turns off both HS and LS FETs when junction temperature is above $160^{\circ} \mathrm{C}$ (typ.). A hysteresis of $30^{\circ} \mathrm{C}$ is implemented, so when junction temperature drops below $130{ }^{\circ} \mathrm{C}$, the device restarts by initiating the soft-start sequence again.

## Soft Startup

SiP12107 deploys an internally regulated soft-start sequence to realize a monotonic startup ramp without any output overshoot. Once $A V_{I N}$ is above UVLO level ( 2.55 V typ.). Both the reference and $V_{\text {OUT }}$ will ramp up slowly to regulation in 1 ms (typ.) with the reference going from 0 V to 0.6 V and $\mathrm{V}_{\text {OUT }}$ rising monotonically to the programmed output voltage.
During soft-start period, OCP is activated. OVP and short-circuit protection are not active until soft-start is complete.

## Pre-bias Startup

In case of pre-bias startup, output is monitored through FB pin. If the sensed voltage on FB is higher than the internal reference ramp value, control logic prevents HS and LS FET from switching to avoid negative output voltage spike and excessive current sinking through LS FET.

## Power Good (PG)

SiP12107's power good is an open-drain output. Pull PG pin high up to 5 V through a 10 K resistor to use this signal. Power good window is shown in the below diagram. If voltage level on FB pin is out of this window, PG signal is de-asserted by pulling down to GND.


Fig. 7 - PG Window and Timing Diagram

## DESIGN PROCEDURE

The design process of the SiP 12107 is quite straight forward. Only few passive components such as output capacitors, inductor and $R_{\text {on }}$ resistor need to be selected.
The following paragraph describes the selection procedure for these peripheral components for a given operating conditions.
In the next example the following definitions apply:
$\mathrm{V}_{\text {INmax. }}$ : the highest specified input voltage
$V_{\text {INmin. }}$ : the minimum effective input voltage subject to voltage drops due to connectors, fuses, switches, and PCB traces
There are two values of load current to evaluate - continuous load current and peak load current.
Continuous load current relates to thermal stress considerations which drive the selection of the inductor and input capacitors.
Peak load current determines instantaneous component stresses and filtering requirements such as inductor saturation, output capacitors, and design of the current limit circuit.
The following specifications are used in this design:

- $\mathrm{V}_{\mathrm{IN}}=3.3 \mathrm{~V} \pm 10 \%$
- $\mathrm{V}_{\text {OUT }}=1.2 \mathrm{~V}_{ \pm} \%$
- $\mathrm{f}_{\mathrm{Sw}}=1 \mathrm{MHz}$
- Load $=3$ A maximum


## Setting Switching Frequency

Selection of the switching frequency requires making a trade-off between the size and cost of the external filter components (inductor and output capacitor) and the power conversion efficiency. The desired switching frequency, 1 MHz was chosen based on optimizing efficiency while maintaining a small footprint and minimizing component cost.
In order to set the design for 1 MHz switching frequency, ( $\mathrm{R}_{\mathrm{ON}}$ ) resistor which determines the on-time (indirectly setting the frequency) needs to be calculated using the following equation.

$$
\mathrm{R}_{\mathrm{ON}}=\frac{1}{\mathrm{~F}_{\mathrm{SW}} \times \mathrm{K}}=\frac{1}{1 \times 10^{6} \times 9,6 \times 10^{-12}} \cong 105 \mathrm{k} \Omega
$$

## INDUCTOR SELECTION

In order to determine the inductance, the ripple current must first be defined. Cost, PCB size, output ripple, and efficiency are all used in the selection process. Low inductor values result in smaller size and allow faster transient performance but create higher ripple current which can reduce efficiency. Higher inductor values will reduce the ripple current while compromising the efficiency (higher DCR) and transient response.
The ripple current will also set the boundary for power-save operation. The switcher will typically enter power-save mode when the load current decreases to $1 / 2$ of the ripple current. For example, if ripple current is 1 A then power-save operation will typically start at loads approaching 0.5 A. Alternatively, if ripple current is set at $40 \%$ of maximum load current, then power-save will start for loads less than ~ 20 \% of maximum current.

Setting the ripple current $20 \%$ to $50 \%$ of the maximum load current provides an optimal trade-off of the areas mentioned above.

The equation for determining inductance is shown next.

## Example

In this example, the inductor ripple current is set equal to $30 \%$ of the maximum load current. Thus ripple current will be $30 \% \times 3 \mathrm{~A}$ or 0.9 A . To find the minimum inductance needed, use the $\mathrm{V}_{\mathbb{I N}}$ and $\mathrm{t}_{\mathrm{ON}}$ values that correspond to $V_{\text {INmax. }}$

$$
\mathrm{L}=\left(\mathrm{V}_{\mathrm{IN}}-\mathrm{V}_{\mathrm{OUT}}\right) \times \frac{\mathrm{t}_{\mathrm{ON}}}{\Delta \mathrm{i}}
$$

Plugging numbers into the above equation we get

$$
\mathrm{L}=(3.63 \mathrm{~V}-1.2 \mathrm{~V}) \times \frac{330 \times 10^{-9} \mathrm{~S}}{0.9 \mathrm{~A}}=0.891 \mu \mathrm{H}
$$

A slightly larger value of $1 \mu \mathrm{H}$ is selected which is a standard value. This will decrease the maximum ripple current by $10 \%$. Note that the inductor must be rated for the maximum DC load current plus $1 / 2$ of the ripple current. The actual ripple current using the chosen $1 \mu \mathrm{H}$ inductor comes out to be.

$$
\Delta i=(3.63 \mathrm{~V}-1.2 \mathrm{~V}) \times \frac{330 \mathrm{~ns}}{1 \mu \mathrm{H}}=0.8 \mathrm{~A}
$$

## Output Capacitance Calculation

The output capacitance is usually chosen to meet transient requirements. A worst-case load release, from maximum load to no load at the exact moment when inductor current is at the peak, determines the required capacitance. If the load release is instantaneous (load changes from maximum to zero in $<1 / \mathrm{f}_{\text {SW }} \mu \mathrm{s}$ ), the output capacitor must absorb all the inductor's stored energy. This will approximately cause a peak voltage on the capacitor according to the following equation.

$$
\mathrm{C}_{\text {OUTmin. }}=\frac{\mathrm{Lx}\left(\mathrm{I}_{\text {OUT }}+\frac{1}{2} \times \mathrm{I}_{\text {RIPPLEmax. }}\right)^{2}}{\left(\mathrm{~V}_{\text {peak }}\right)^{2}-\left(\mathrm{V}_{\text {OUT }}\right)^{2}}
$$

Assuming a peak voltage $\mathrm{V}_{\text {PEAK }}$ of $1.3 \mathrm{~V}(100 \mathrm{mV}$ rise upon load release), and a 3 A load release, the required capacitance is shown by the next equation.

$$
\mathrm{C}_{\text {OUTmin. }}=\frac{1 \mu \mathrm{H} \times(3 \mathrm{~A}+0.5 \times(81 \mathrm{~A}))^{2}}{(1.3 \mathrm{~V})^{2}-(1.2 \mathrm{~V})^{2}}=46.37 \mu \mathrm{~F}
$$

If the load release is relatively slow, the output capacitance can be reduced. Using MLCC ceramic capacitors we will use $3 \times 22 \mu \mathrm{~F}$ or $66 \mu \mathrm{~F}$ as the total output capacitance.

## STABILITY CONSIDERATIONS

Using the output capacitance as a starting point for compensation values. Then, taking Bode plots and transient response measurements we can fine tune the compensation values.
Setting the crossover frequency to $1 / 5$ of the switching frequency:
$\mathrm{f}_{0}=\mathrm{f}_{\mathrm{sw}} / 5=1 \mathrm{MHz} / 5=200 \mathrm{kHz}$
Setting the compensation zero at $1 / 5$ to $1 / 10$ the crossover frequency for the phase boost:

$$
F_{Z}=\frac{1}{2 \pi \times R_{C} \times C_{C}}=\frac{F_{0}}{5}
$$

Setting $\mathrm{C}_{\mathrm{C}}=1 \mathrm{nF}$ and solve for $\mathrm{R}_{\mathrm{C}}$

$$
\mathrm{R}_{\mathrm{C}}=\frac{5}{2 \pi \times \mathrm{C}_{\mathrm{C}} \times \mathrm{F}_{0}}=\frac{5}{2 \pi \times 1 \mathrm{nF} \times 200 \mathrm{~K}}=4 \mathrm{~K}
$$

## SWITCHING FREQUENCY VARIATIONS

The switching frequency variation in COT can be mainly attributed to the increase in conduction losses as the load increases. The on time is "ideally constant" so the controller must account for losses by reducing the off time which increases the overall duty cycle. Hence the $\mathrm{f}_{\mathrm{Sw}}$ will tend to increase with load.
In power save mode (PSM) the IC will run in pulse skip mode at light loads. As the load increases the $\mathrm{f}_{\mathrm{SW}}$ will increase until it reaches the nominal set $\mathrm{f}_{\mathrm{Sw}}$. This transition occurs approximately when the load reaches to $20 \%$ of the full load current.


Fig. 8 - Reference Board Schematic

SiP12107

| BILL OF MATERIALS |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| ITEM | QTY. | REFERENCE | PART | VOLTAGE | PCB FOOTPRINT | PART NUMBER | MANUFACTURER |
| 1 | 4 | C1, C2, C3, C4 | $22 \mu \mathrm{~F}$ | 16 V | SM/C_1210 | GRM32ER71C226ME18L | Murata |
| 2 | 1 | C5 | DNP | 50 V | SM/C_0603 | - | - |
| 3 | 2 | C7, C13 | $220 \mu \mathrm{~F}$ | 25 V | 594D-R TYPE | 594D227X0016R2T | Vishay |
| 4 | 3 | C8, C19, C21 | $0.1 \mu \mathrm{~F}$ | 50 V | SM/C_0603 | VJ0603Y104KXACW1BC | Vishay |
| 5 | 3 | C9, C10, C11 | $22 \mu \mathrm{~F}$ | 6.3 V | SM/C_1210 | GCM32ER70J476KE19L | Murata |
| 6 | 3 | C12, C29, C30 | DNP | 6.3 V | SM/C_1210 | - | - |
| 7 | 2 | C14, C20 | $10 \mu \mathrm{~F}$ | 16 V | SM/C_1206 | C1206C106K4RACTU | Taiyo Yuden |
| 8 | 1 | C15 | $0.1 \mu \mathrm{~F}$ | 50 V | SM/C_0402 | VJ0603Y104KXACW1BC | Vishay |
| 9 | 1 | C16 | 68 pF | 50 V | SM/C_0603 | VJ0402A680JNAAJ | Vishay |
| 10 | 1 | C17 | $0.1 \mu \mathrm{~F}$ | 50 V | SM/C_0402 | VJ0402Y104KXACW1BC | Vishay |
| 11 | 1 | C18 | 68 pF | 50 V | SM/C_0402 | VJ0402A680JNAAJ | Vishay |
| 12 | 1 | C23 | $2.2 \mu \mathrm{~F}$ | 10 V | SM/C_0603 | GRM188R71A225KE15D | Murata |
| 13 | 1 | C26 | DNP | 50 V | SM/C_0402 | - | - |
| 14 | 1 | C27 | 1 nF | 50 V | SM/C_0402 | VJ0402Y102KXACW1BC | Vishay |
| 29 | 1 | L1 | $1 \mu \mathrm{H}$ | - | IHLP2525 | IHLP2525DZER1R0M01 | Vishay |
| 30 | 1 | Q1 | - | 30 V | SO-8 | Si4812BDY | Vishay |
| 31 | 1 | R1 | 3R01 | 200 V | C_2512 | CRCW25123R01FKTA | Vishay |
| 32 | 4 | R2, R3, R5, R9 | 100K | 50 V | SM/C_0603 | CRCW0603100KFKEA | Vishay |
| 33 | 1 | R6 | 100 | 50 V | SM/C_0402 | TNPW0402100RBEED | Vishay |
| 34 | 1 | R7 | 5K11 | 50 V | SM/C_0603 | CRCW06035K11FKEA | Vishay |
| 35 | 1 | R8 | OR | 50 V | SM/C_0402 | CRCW04020000FKTA | Vishay |
| 36 | 1 | R10 | 5K11 | - | SM/C_0603 | CRCW06035K11FKEA | - |
| 37 | 1 | R11 | 100 | 50 V | SM/C_0603 | TNPW0402100RBEED | Vishay |
| 38 | 1 | R12 | 10K | 50 V | SM/C_0603 | CRCW060310KOFKEA | Vishay |
| 39 | 1 | R14 | 100K | 50 V | SM/C_0603 | CRCW0603100KFKEA | Vishay |
| 40 | 1 | R42 | 2K | 50 V | SM/C_0603 | CRCW06032K00FKEA | Vishay |
| 41 | 1 | R43 | DNP | - | SM/C_0805 | - |  |
| 42 | 1 | R44 | OR | 50 V | SM/C_0603 | CRCW06030000ZOEA | Vishay |
| 43 | 1 | R45 | OR | 50 V | SM/C_0402 | CRCW04020000FKTA | Vishay |
| 44 | 1 | U1 | - | - | QFN3X3_16 L | SiP12107 | Vishay |
| 45 | 1 | J1 | $\mathrm{V}_{\text {IN }}$ |  | PROBE PIN | PK007-015 | Lecroy |
| 46 | 1 | J2 | LX |  | PROBE PIN | PK007-015 | Lecroy |
| 47 | 1 | J3 | $\mathrm{V}_{\text {IN }}$ |  | Power connector | 575-6 | Keystone |
| 48 | 1 | J4 | $\mathrm{V}_{\text {OUT }}$ |  | Power connector | 575-6 | Keystone |
| 49 | 1 | J5 | $\mathrm{V}_{\text {OUT }}$ |  | PROBE PIN | PK007-015 | Lecroy |
| 50 | 1 | J6 | $\mathrm{V}_{\text {IN_GND }}$ |  | Power connector | 575-6 | Keystone |
| 51 | 1 | J7 | Vo_GND |  | Power connector | 575-6 | Keystone |
| 52 | 1 | J8 | EN |  | Control PIN | 1573-3 | Keystone |
| 53 | 1 | J9 | MODE |  | Control PIN | 1573-3 | Keystone |
| 54 | 1 | J10 | PGD |  | Probe PIN | 1573-3 | Keystone |
| 55 | 1 | J11 | Step_I_Sense |  | Probe PIN | 1573-3 | Keystone |
| 56 | 1 | J12 | LDT |  | SMA test connector | PK007-015 | Lecroy |
| 57 | 1 | J13 | CH2 |  | Test point | 1573-3 | Keystone |
| 58 | 1 | J14 | CH1 |  | Test point | 1573-3 | Keystone |

SiP12107
Vishay Siliconix

## PCB LAYOUT OF REFERENCE BOARD



Fig. 9 - Top Layer


Fig. 10 - Inner Layer1


Fig. 11 - Bottom Layer


Fig. 12 - Inner Layer2

SiP12107

| PRODUCT SUMMARY |  |
| :--- | :---: |
| Part number | SiP12107 |
| Description | $3 \mathrm{~A}, 2.8 \mathrm{~V}$ to 5.5 V input, 4 MHz synchronous buck regulator |
| Input voltage min. (V) | 2.8 |
| Input voltage max. (V) | 6 |
| Output voltage min. (V) | 0.6 |
| Output voltage max. (V) | 5.5 |
| Continuous current (A) | 3 |
| Switch frequency min. (kHz) | 200 |
| Switch frequency max. (kHz) | 4000 |
| Pre-bias operation (yes /no) | Yes |
| Internal bias reg. (yes /no) | Yes |
| Compensation | External |
| Enable (yes / no) | Yes |
| PGood (yes / no) | Yes |
| Overcurrent protection | Fixed |
| Protection | OVP, OCP, UVP/SCP, OTP, UVLO |
| Light load mode | Powersave |
| Peak efficiency (\%) | 95 |
| Package type | QFN16-33G |
| Package size (W, L, H) (mm) | 3.0 x 3.0 x 0.8 |
| Status code | 2 |
| Product type | Computing, consumer, networking, industrial, healthcare |
| Applications |  |

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